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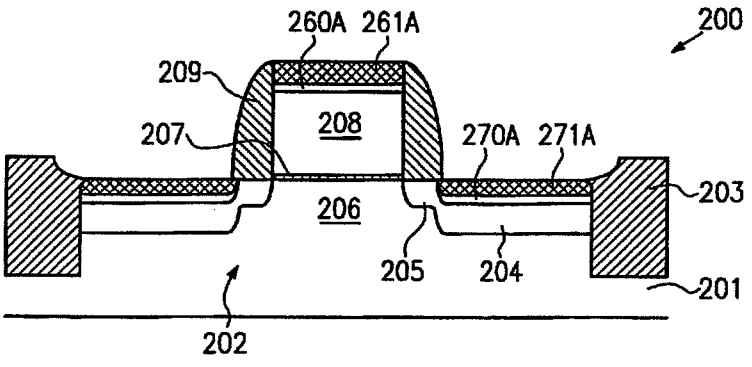
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(54) Title: A SEMICONDUCTOR DEVICE HAVING A NICKEL/COBALT SILICIDE REGION FORMED IN A SILICON REGION



(57) Abstract: By forming a buried nickel silicide layer (260A) followed by a cobalt silicide layer (261A) in silicon containing regions, such as a gate electrode of a field effect transistor, the superior characteristics of both silicides may be combined so as to provide the potential for further device scaling without unduly compromising the sheet resistance and the contact resistance of scaled silicon circuit features.

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